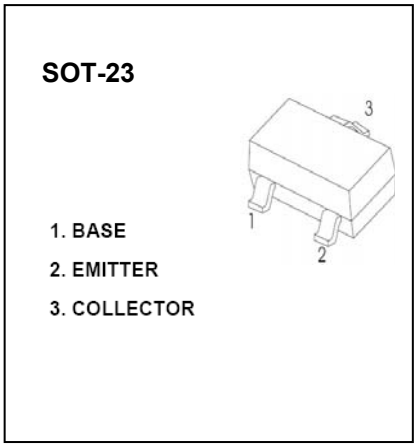
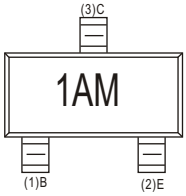
TRANSISTOR(NPN)



FEATURES

- Complementary Type The PNP Transistor MMBT3906 is Recommended
- Epitaxial Planar Die Construction

MARKING: 1AM



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	200	mA
P_C	Total Device Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	625	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55 ~ +150	℃

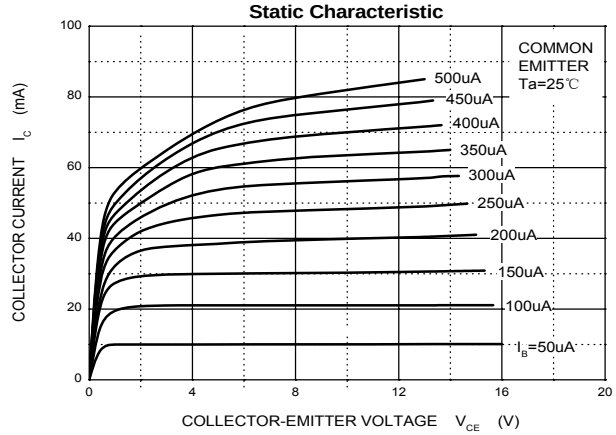
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 10μA, I_E=0	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1mA, I_B=0	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	6		V
Collector cut-off current	I_{CBO}	V_{CB}=60V, I_E=0		0.1	μA
Collector cut-off current	I_{CEX}	V_{CE}=30V,$V_{BE(off)}$=3V		50	nA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0		0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C=10mA	100	300	
	$h_{FE(2)}$	V_{CE}=1V, I_C= 50mA	60		
	$h_{FE(3)}$	V_{CE}=1V, I_C= 100mA	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA, I_B= 5mA		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= 50mA, I_B= 5mA		0.95	V
Transition frequency	f_T	V_{CE}=20V, I_C=10mA,f=100MHz	300		MHz
Delay Time	t_d	V_{CC}=3V,V_{BE}=-0.5V		35	nS
Rise Time	t_r	I_C=10mA, I_{B1}=-I_{B2}=1.0mA		35	nS
Storage Time	t_s	V_{CC}=3V,I_C=10mA,		200	nS
Fall Time	t_f	I_{B1}=-I_{B2}=1mA		50	nS

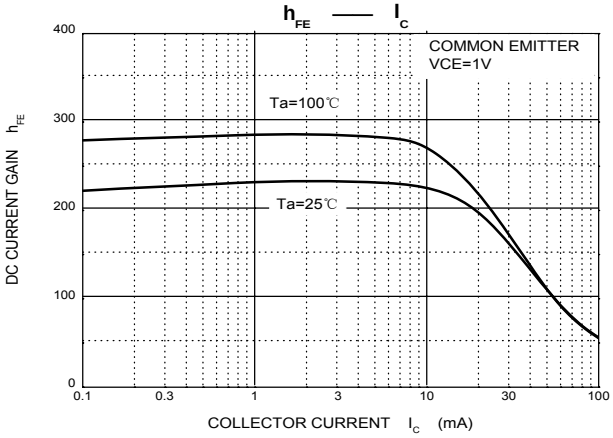
CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	
Range	100-200	200-300	

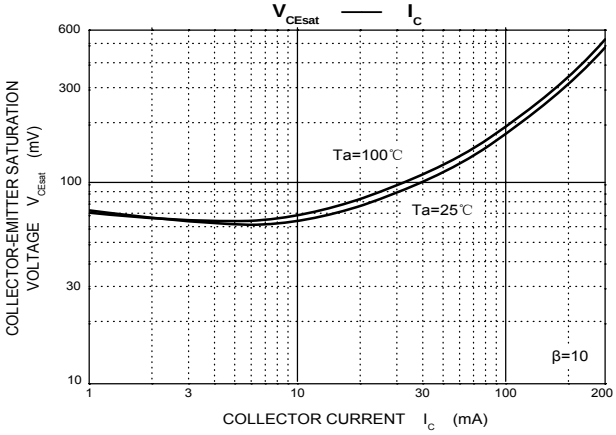
Static Characteristic



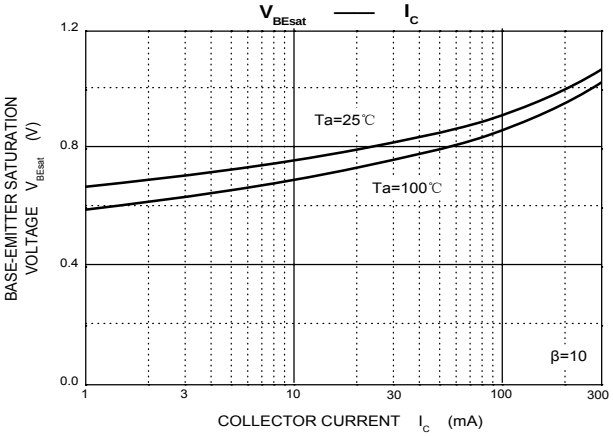
h_{FE} —— I_C



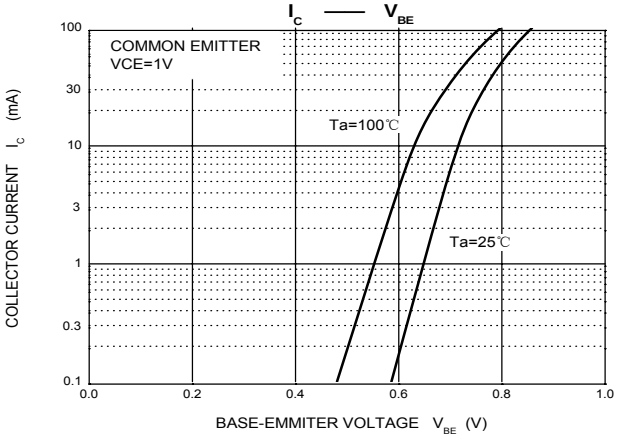
V_{CEsat} —— I_C



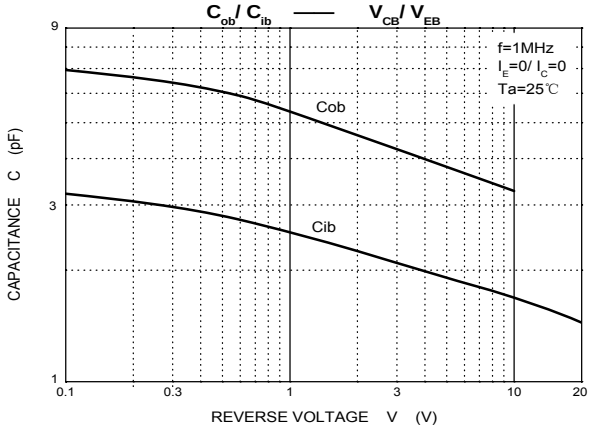
V_{BEsat} —— I_C



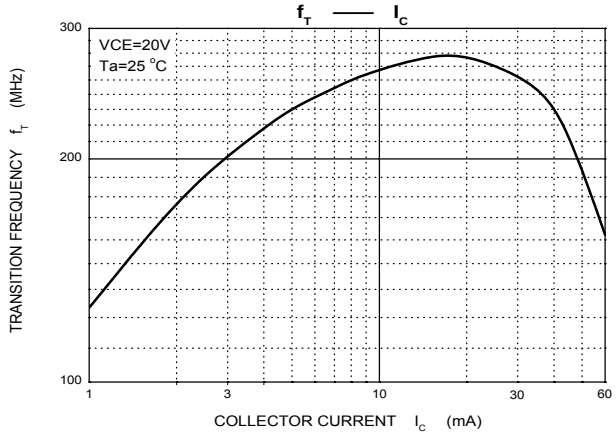
I_C —— V_{BE}



C_{ob} / C_{ib} —— V_{CB} / V_{EB}



f_T —— I_C



Pc —— Ta

